STPS61L60C

Power Schottky rectifier

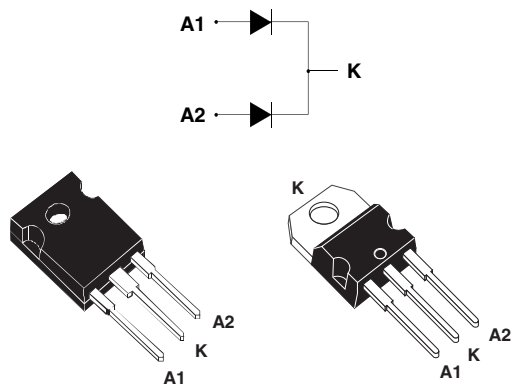
Features

- High current capability
- Avalanche rated
- Low forward voltage drop current
- High frequency operation

Description

Dual center tap schottky rectifier suited for high frequency switch mode power supplies.

Packaged in TO-247 and TO-220AB, this device provides desktop SMPS designers with a low forward voltage drop device, and reduced leakage current, with the objective of making the application compliant with environmental care standards, or suitable for 80+ requirements.



TO-247
STPS61L60CW

TO-220AB
STPS61L60CT

Table 1. Device summary

$I_{F(AV)}$	2 x 30 A
V_{RRM}	60 V
T_j (max)	150 °C
V_F(typ)	0.560 V

1 Characteristics

Table 2. Absolute ratings (limiting values per diode at 25 °C unless otherwise specified)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			60	V
$I_{F(RMS)}$	RMS forward voltage			50	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$	T_c = 125 °C T_c = 120 °C	Per diode Per device	30 60	A
I_{FSM}	Surge non repetitive forward current	t_p = 10 ms sinusoidal	T0-247 T0-220AB	530 400	A
P_{ARM}	Repetitive peak avalanche power	t_p = 1 µs Tj = 25 °C		11500	W
T_{stg}	Storage temperature range			-65 to + 175	°C
T_j	Maximum operating junction temperature (1)			150	°C

1. $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ condition to avoid runaway for a diode on its own heatsink

Table 3. Thermal resistances

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	TO-247	Per diode Total	0.95 0.6	°C/W
		TO-220AB	Per diode Total	1.1 0.7	
$R_{th(c)}$	Coupling		TO-247	0.25	
			TO-220AB	0.3	

When the diodes 1 and 2 are used simultaneously :

$\Delta Tj(diode\ 1) = P(diode1) \times R_{th(j-c)}(Per\ diode) + P(diode\ 2) \times R_{th(c)}$.

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I_R(1)	Reverse leakage current	T_j = 25 °C	$V_R = V_{RRM}$	-	-	0.8	mA
		T_j = 125 °C		-	150	350	
V_F(2)	Forward voltage drop	T_j = 25 °C	I_F = 5 A	-	0.360	-	V
		T_j = 125 °C	I_F = 5 A	-	0.255	-	
		T_j = 25 °C	I_F = 15 A	-	0.460	0.540	
		T_j = 125 °C	I_F = 15 A	-	0.415	0.480	
		T_j = 25 °C	I_F = 30 A	-	0.580	0.660	
		T_j = 125 °C	I_F = 30 A	-	0.560	0.620	

1. Pulse test: t_p = 5 ms, $\delta < 2\%$
2. Pulse test: t_p = 380 µs, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$P = 0.44 \times I_{F(AV)} + 0.006 \times I_F^2{}_{(RMS)}$

Figure 1. Average forward power dissipation vs. average forward current (per diode)

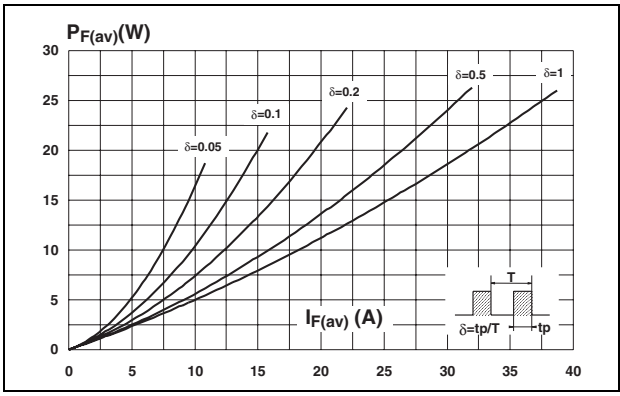


Figure 2. Average forward current vs. ambient temperature (δ = 0.5, per diode)

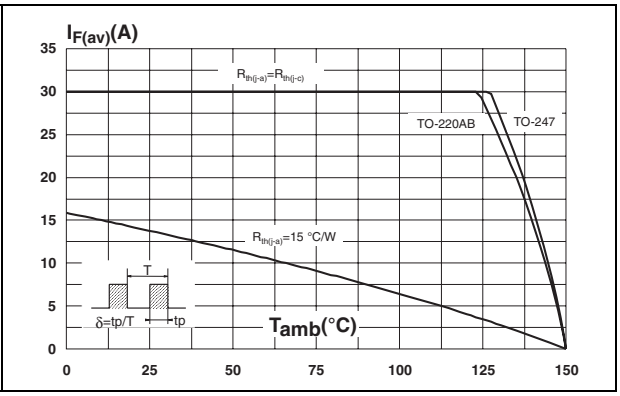


Figure 3. Normalized avalanche power derating vs. pulse duration

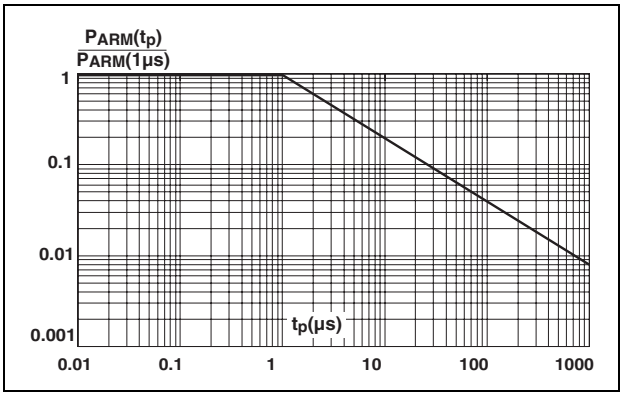


Figure 4. Normalized avalanche power derating vs. junction temperature

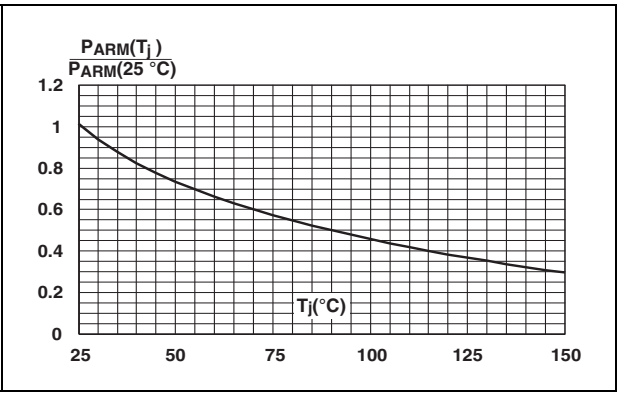


Figure 5. Non repetitive surge peak forward current vs. overload duration (max. values, per diode, TO-247)

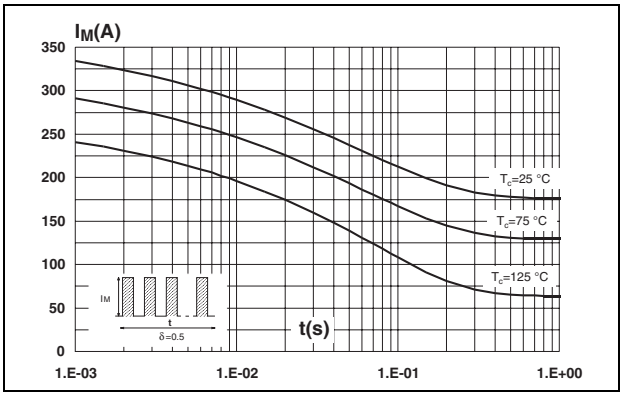
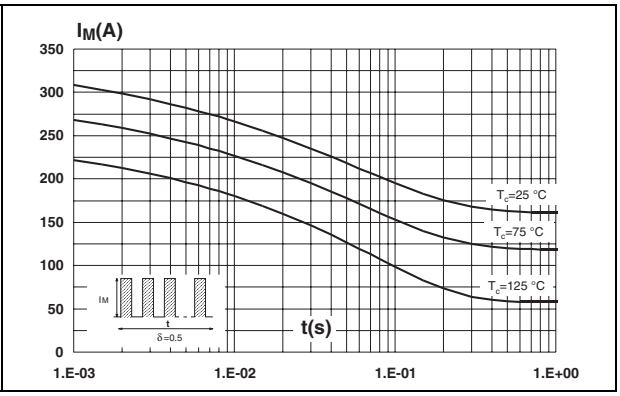


Figure 6. Non repetitive surge peak forward current vs. overload duration (max. values, per diode, TO-220AB)



3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STPS61L60CW	STPS61L60CW	TO-247	4.4 g	30	Tube
STPS61L60CT	STPS61L60CT	TO-220AB	2.23 g	30	Tube